

Silicon PNP Power Transistors

TIP514

DESCRIPTION

- With TO-66 package
- Low collector saturation voltage
- Wide area of safe operation

APPLICATIONS

- For use in high-frequency drivers
In audio amplifiers

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

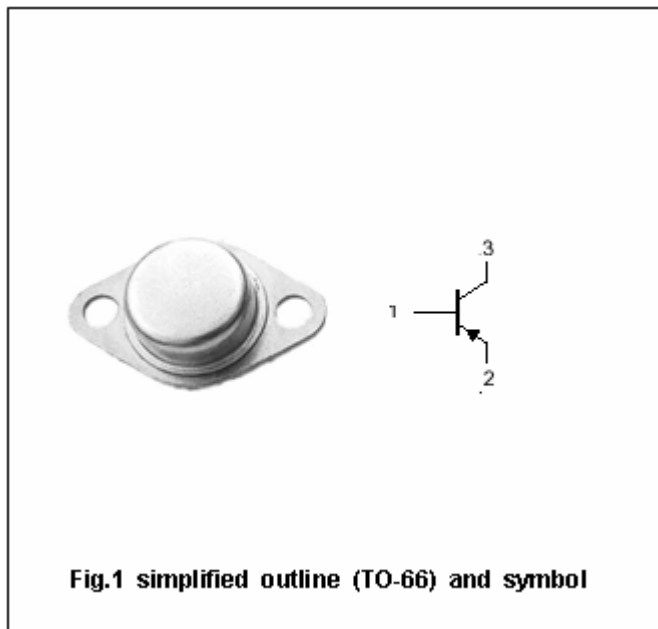


Fig.1 simplified outline (TO-66) and symbol

ABSOLUTE MAXIMUM RATINGS(T_c=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-150	V
V _{CEO}	Collector-emitter voltage	Open base	-150	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-5	A
P _D	Total power dissipation	T _c =100°C	20	W
		T _a =100°C	2	
T _j	Junction temperature		175	°C
T _{stg}	Storage temperature		-55~175	°C

Silicon PNP Power Transistors

TIP514

CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =-10mA ; I _B =0	-150			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-1mA ; I _C =0	-5			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =-5A; I _B =-0.5A			-2.0	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C =-5A; I _B =-0.5A			-2.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-150V; I _E =0			-10	μA
I _{CEO}	Collector cut-off current	V _{CE} =-150V; I _B =0			-100	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-10	μA
h _{FE}	DC current gain	I _C =-2.5A ; V _{CE} =-4V	30		150	
f _T	Transition frequency	I _C =-0.5A ; V _{CE} =-4V	40			MHz

Silicon PNP Power Transistors

TIP514

PACKAGE OUTLINE

